

1. Scope :

This specification applies to P/N silicon zener diode chips,
Device NO. SD-30712GL-A

2. Structure :

- 2-1. Planar type : P/N Diode
- 2-2. Electrodes :
Top side : Gold pad.
Back side : Gold layer.

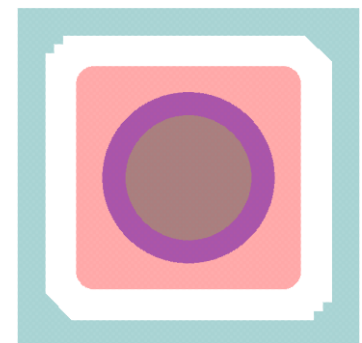
3. Size :

- 3-1. Chip size :
3-1-1. Top side: $170 \pm 20 \mu\text{m} \times 170 \pm 20 \mu\text{m}$ ($6.69 \pm 0.8 \text{ mils} \times 6.69 \pm 0.8 \text{ mils}$).
3-1-2. Bottom side: $180 \pm 20 \mu\text{m} \times 180 \pm 20 \mu\text{m}$ ($7.08 \pm 0.8 \text{ mils} \times 7.08 \pm 0.8 \text{ mils}$).
- 3-2. Chip thickness : $130 \pm 13 \mu\text{m}$ ($5.12 \pm 0.5 \text{ mils}$).
- 3-3. Active area : $125 \pm 10 \mu\text{m} \times 125 \pm 10 \mu\text{m}$ ($4.92 \pm 0.4 \text{ mils} \times 4.92 \pm 0.4 \text{ mils}$).
- 3-4. Bonding pad : $\phi 90 \pm 10 \mu\text{m}$ ($\phi 3.54 \pm 0.4 \text{ mils}$).
- 3-5. Pattern drawing : Refer to the attached drawing.
- 3-6. Fiducial mark does not apply any characteristics or any incoming inspection.

4. Electrical characteristics (Ta = 25 °C)

Parameter	Symbol	Condition	Min.	Typ*1	Max.	Unit
Reverse Leakage Current	I_R	$V_R=4V$ $E_e=0\text{mW}/\text{cm}^2$			100	nA
Zener Voltage	V_Z	$I_Z=5\text{mA}$ $E_e=0\text{mW}/\text{cm}^2$	10	12	14	V
Forward Leakage Current	I_F	$V_F=0.3V$ $E_e=0\text{mW}/\text{cm}^2$			3	nA
Forward Voltage	V_f	$I_F=10\text{mA}$ $E_e=0\text{mW}/\text{cm}^2$	0.8	0.9	1.1	V

*1 Typ. value is for reference only.



Unit: μm

